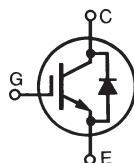


BiMOSFET™ Monolithic Bipolar MOS Transistor

IXBN75N170

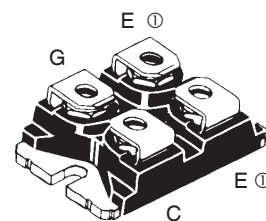
$$\begin{aligned} V_{CES} &= 1700V \\ I_{C90} &= 75A \\ V_{CE(sat)} &\leq 3.1V \end{aligned}$$



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	1700	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}, R_{GE} = 1M\Omega$	1700	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	145	A
I_{C90}	$T_C = 90^\circ\text{C}$	75	A
I_{CM}	$T_C = 25^\circ\text{C}, 1\text{ms}$	680	A
SSOA (RBSOA)	$V_{GE} = 15V, T_{VJ} = 125^\circ\text{C}, R_G = 1\Omega$ Clamped Inductive Load	$I_{CM} = 150$ $V_{CE} \leq 0.8 \cdot V_{CES}$	A
P_C	$T_C = 25^\circ\text{C}$	625	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
T_{SOLD}	1.6 mm (0.062 in.) from Case for 10	260	$^\circ\text{C}$
V_{ISOL}	50/60Hz	$t = 1\text{min}$	2500 V~
	$I_{ISOL} \leq 1\text{mA}$	$t = 1\text{s}$	3000 V~
M_d	Mounting Torque	1.5/13	Nm/lb.in.
	Terminal Connection Torque (M4)	1.3/11.5	Nm/lb.in.
Weight		30	g

SOT-227B, miniBLOC

 E153432



G = Gate, C = Collector, E = Emitter

① either emitter terminal can be used as Main or Kelvin Emitter

Features

- International Standard Package
- High Blocking Voltage
- Isolation Voltage 3000 V~
- High Current Handling Capability
- Anti-Parallel Diode

Advantages

- High Power Density
- Low Gate Drive Requirement
- Easy to Mount with 2 Screws
- Integrated Diode Can Be Used for Protection

Applications

- Capacitor Discharge
- AC Switches
- Switch-Mode and Resonant-Mode Power Supplies
- UPS
- AC Motor Drives

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu\text{A}, V_{GE} = 0V$	1700		V
$V_{GE(th)}$	$I_C = 1.5\text{mA}, V_{CE} = V_{GE}$	2.5		5.5 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}, V_{GE} = 0V$ $T_J = 125^\circ\text{C}$			25 μA 2 mA
I_{GES}	$V_{CE} = 0V, V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = I_{C90}, V_{GE} = 15V, \text{Note 1}$ $T_J = 125^\circ\text{C}$		2.6 3.1	3.1 V V

Symbol Test Conditions

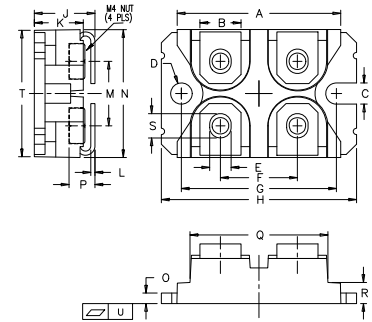
($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

Min. Typ. Max.

g_{IS}	$I_C = I_{C90}, V_{CE} = 10V, \text{Note 1}$	34	56	S
C_{ies}	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$		6930	pF
C_{oes}			400	pF
C_{res}			150	pF
Q_g	$I_C = I_{C90}, V_{GE} = 15V, V_{CE} = 0.5 \bullet V_{CES}$		350	nC
Q_{ge}			50	nC
Q_{gc}			160	nC
$t_{d(on)}$	Resistive load, $T_J = 25^\circ C$ $I_C = I_{C90}, V_{GE} = 15V$ $R_G = 1\Omega, V_{CE} = 0.5 \bullet V_{CES}$		46	ns
t_r			160	ns
$t_{d(off)}$			260	ns
t_f			440	ns
$t_{d(on)}$	Resistive load, $T_J = 125^\circ C$ $I_C = I_{C90}, V_{GE} = 15V$ $R_G = 1\Omega, V_{CE} = 0.5 \bullet V_{CES}$		47	ns
t_r			230	ns
$t_{d(off)}$			260	ns
t_f			580	ns
R_{thJC}				0.20 °C/W
R_{thCS}			0.05	°C/W

SOT-227B miniBLOC (IXBN)



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

Reverse Diode

Symbol Test Conditions

($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

Min. Typ. Max

V_F	$I_F = I_{C90}, V_{GE} = 0V, \text{Note 1}$		3.0	V
t_{rr}	$I_F = 37V, V_{GE} = 0V, -di_F/dt = 100A/\mu s$ $V_R = 100V, V_{GE} = 0V$		1.5	μs
I_{RM}			50	A
Q_{RM}			38.2	μC

Note 1. Pulse test, $t \leq 300\mu s$, duty cycle, $d \leq 2\%$.

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics
@ 25°C

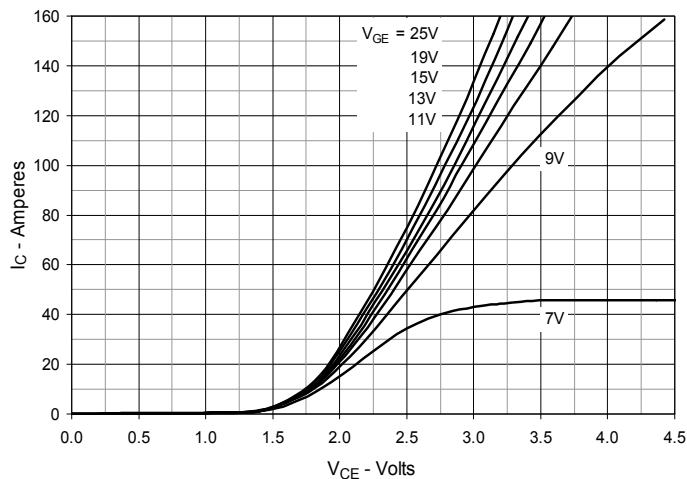


Fig. 2. Extended Output Characteristics
@ 25°C

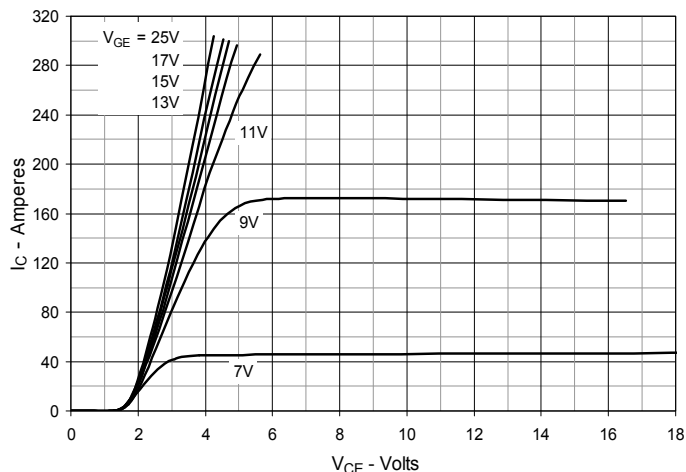


Fig. 3. Output Characteristics
@ 125°C

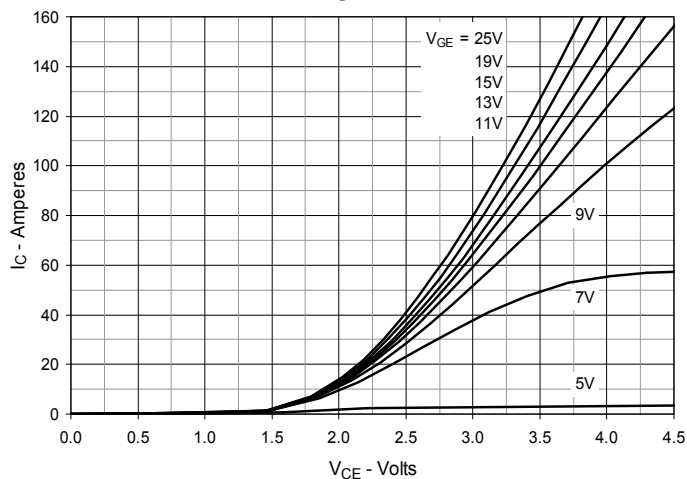


Fig. 4. Dependence of $V_{CE(sat)}$ on
Junction Temperature

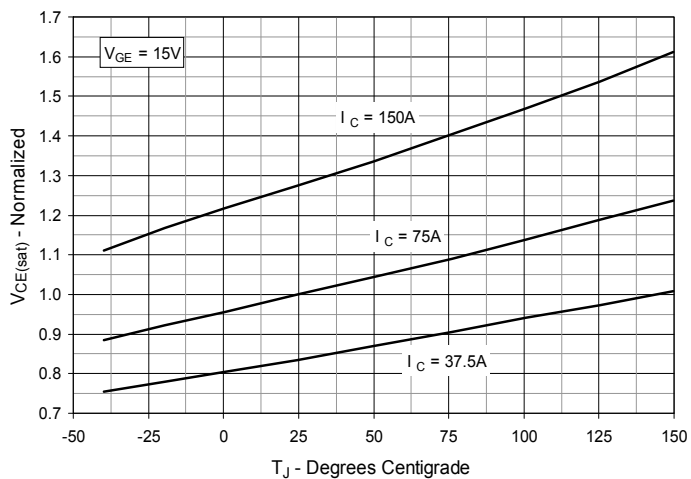


Fig. 5. Collector-to-Emitter Voltage
vs. Gate-to-Emitter Voltage

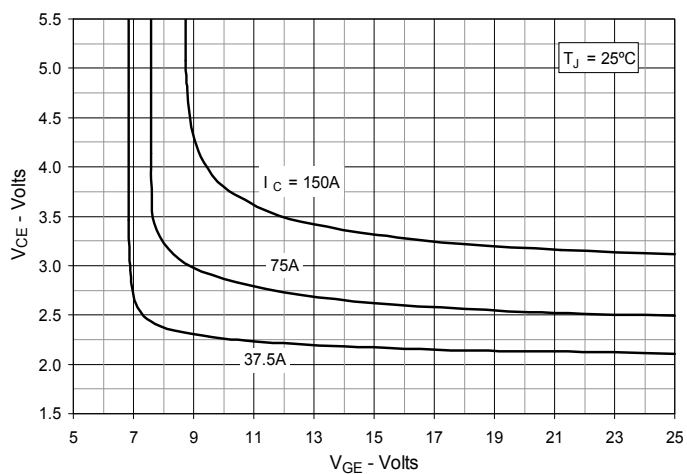


Fig. 6. Input Admittance

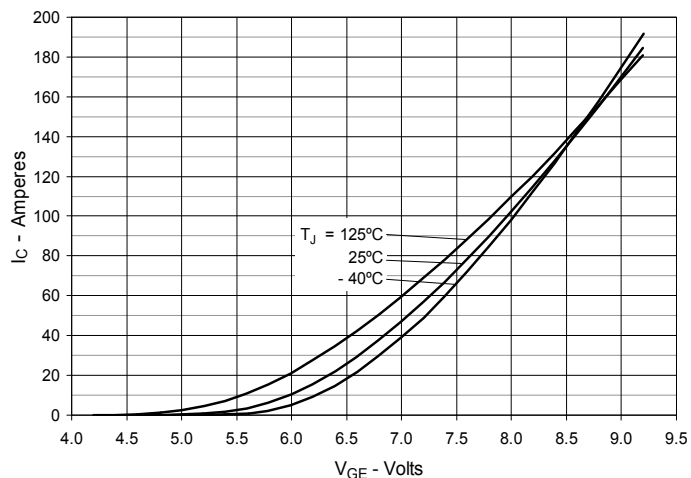


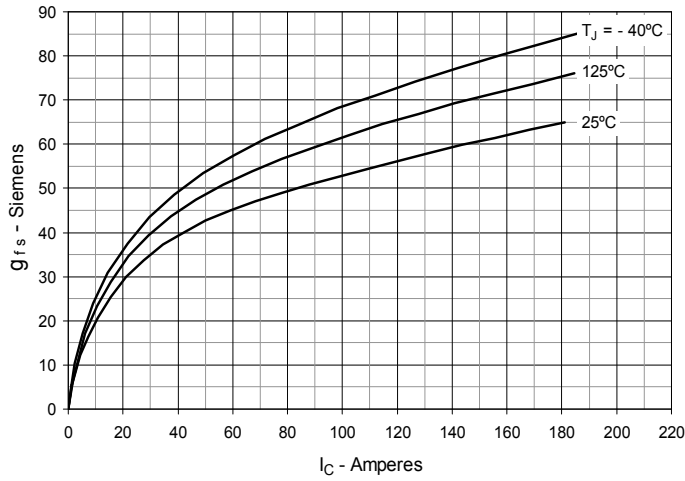
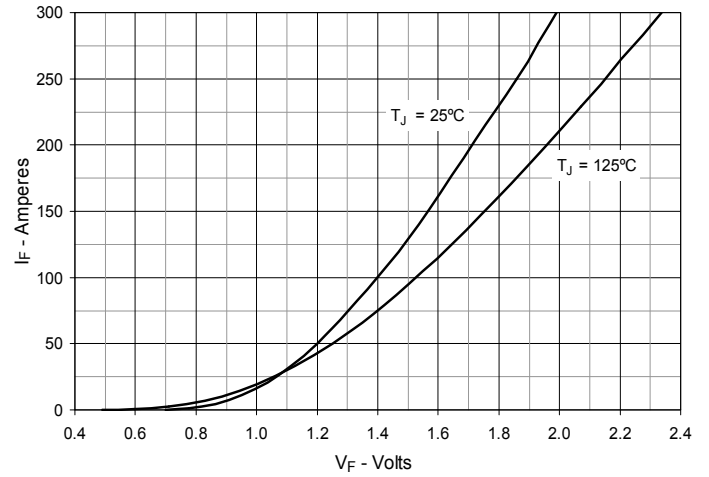
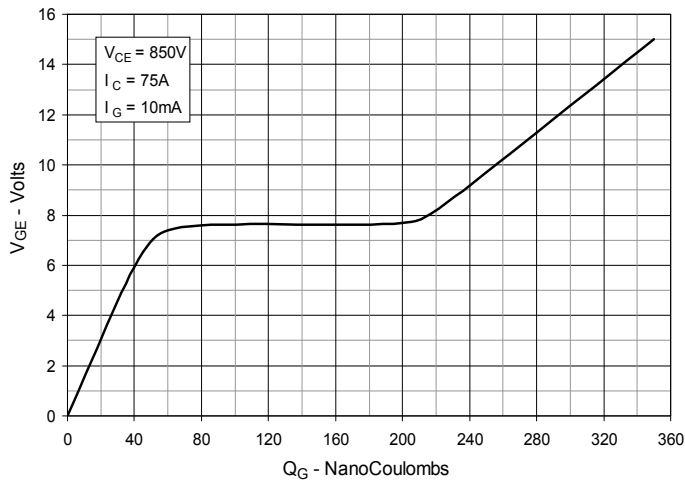
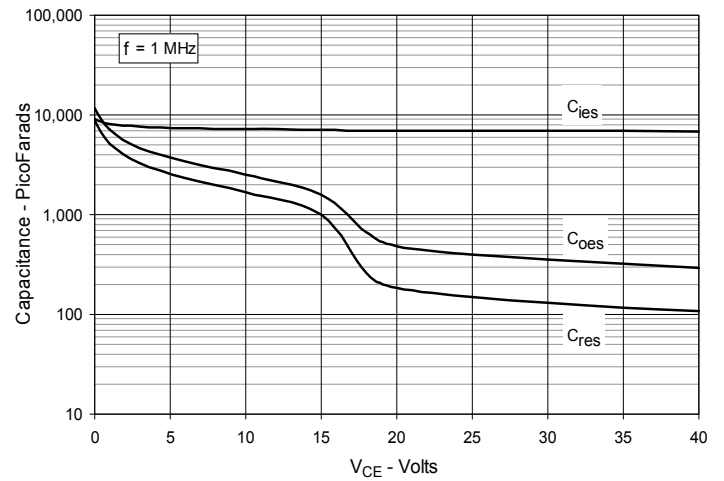
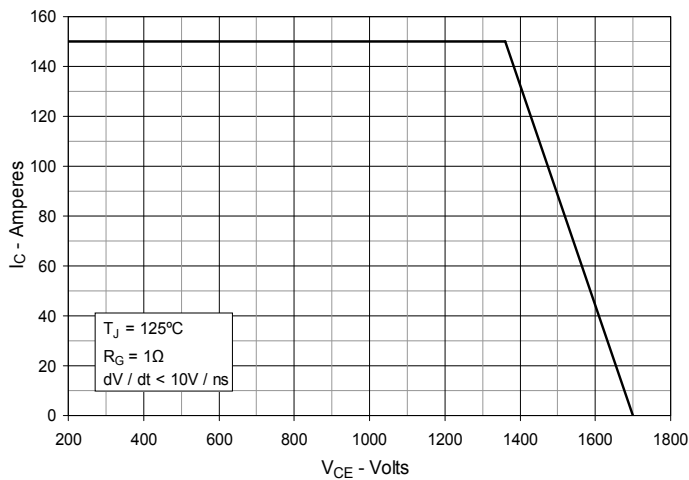
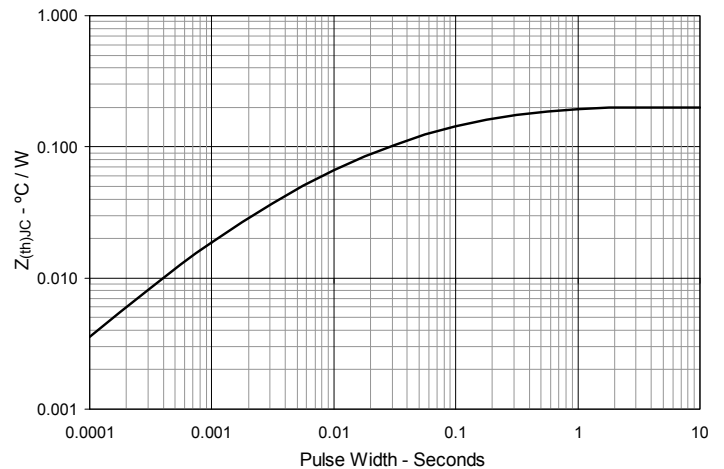
Fig. 7. Transconductance

Fig. 8. Forward Voltage Drop of Intrinsic Diode

Fig. 9. Gate Charge

Fig. 10. Capacitance

Fig. 11. Reverse-Bias Safe Operating Area

Fig. 12. Maximum Transient Thermal Impedance


Fig. 13. Resistive Turn-on
Rise Time vs. Junction Temperature

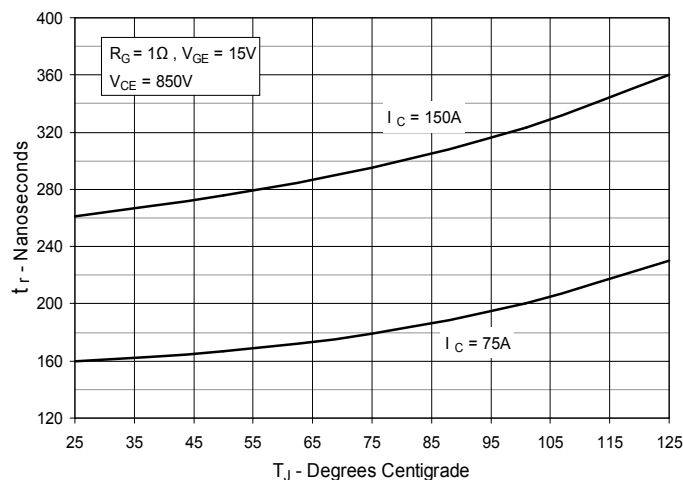


Fig. 14. Resistive Turn-on
Rise Time vs. Collector Current

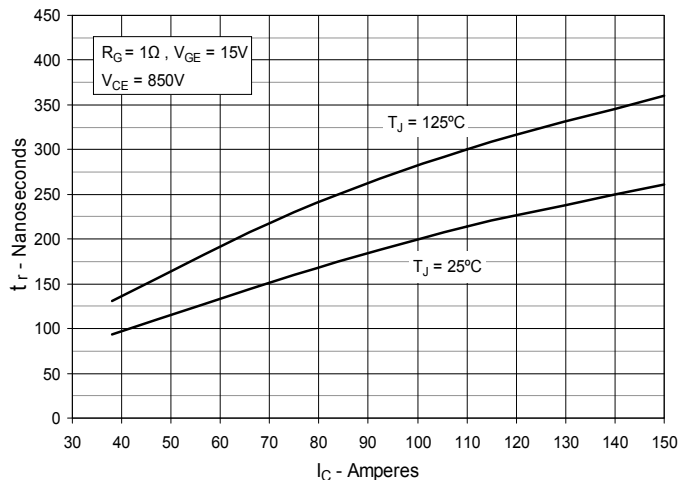


Fig. 15. Resistive Turn-on
Switching Times vs. Gate Resistance

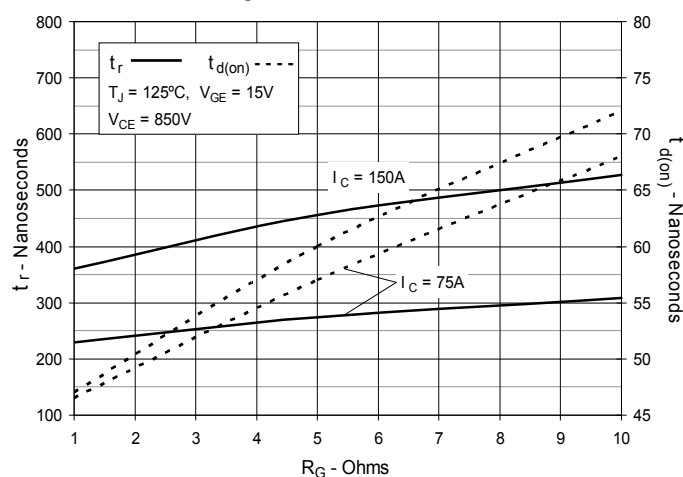


Fig. 16. Resistive Turn-off
Switching Times vs. Junction Temperature

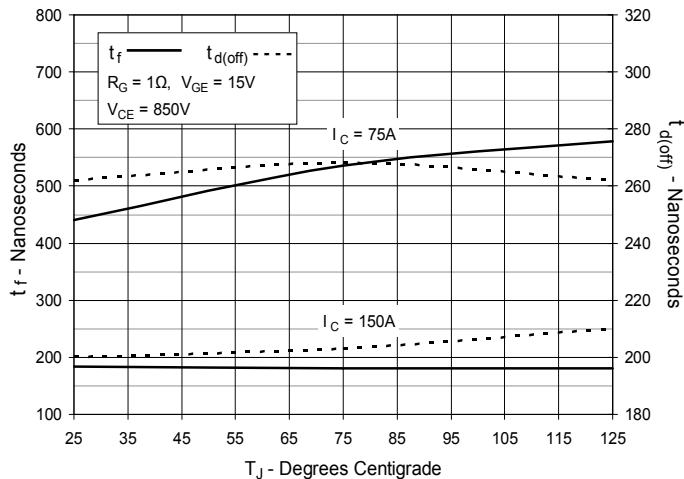


Fig. 17. Resistive Turn-off
Switching Times vs. Collector Current

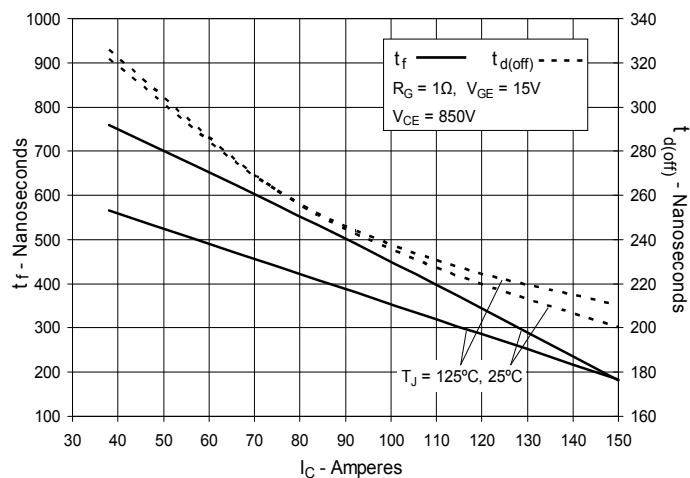


Fig. 18. Resistive Turn-off
Switching Times vs. Gate Resistance

